

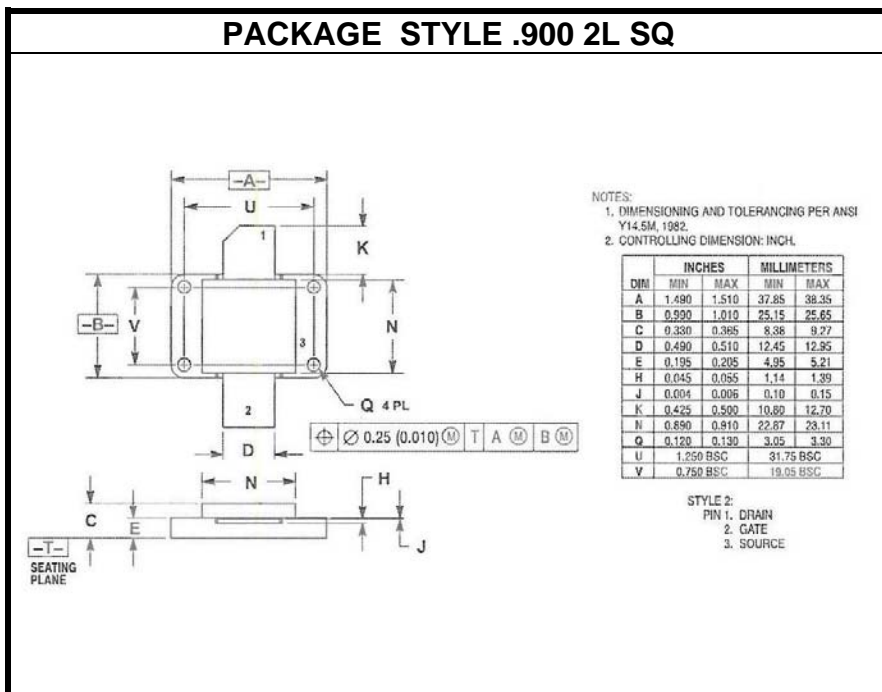
POWER FIELD EFFECT TRANSISTOR

DESCRIPTION:

The **ASI MRF157** is an Enhancement-Mode N-Channel MOS designed for linear large-signal output stages to 80 MHz.

MAXIMUM RATINGS

I_D	60 Adc
V_{DSS}	125 V
V_{DGO}	125 V
V_{GS}	±40 V
P_{DISS}	1350 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.13 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{(BR)DSS}	I _D = 100 mA V _{GS} = 0 V	125			V
I_{DSS}	V _{DSS} = 50 V V _{GS} = 0 V			20	mA
I_{GSS}	V _{GS} = 20 V V _{DS} = 0 V			5.0	μA
V_{GS(th)}	V _{DS} = 10 V I _D = 100 mA	1.0		5.0	V
V_{DS(on)}	V _{DS} = 10 V I _D = 40 A	1.0		5.0	V
g_{fs}	V _{DS} = 10 V I _D = 20 A	16			mhos
C_{iss}	V _{DS} = 50 V V _{GS} = 0 V f = 1.0 MHz		1800		pF
C_{oss}			750		
C_{rss}			75		
G_{ps}	V _{DD} = 50 V I _{DQ} = 800 mA f = 30 MHz	18	21		dB
η	P _{out} = 600 W	45	50		%
IMD_(d3)			-25		dB

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